



CET-MOS

The best of power team

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<https://www.cet-mos.com>

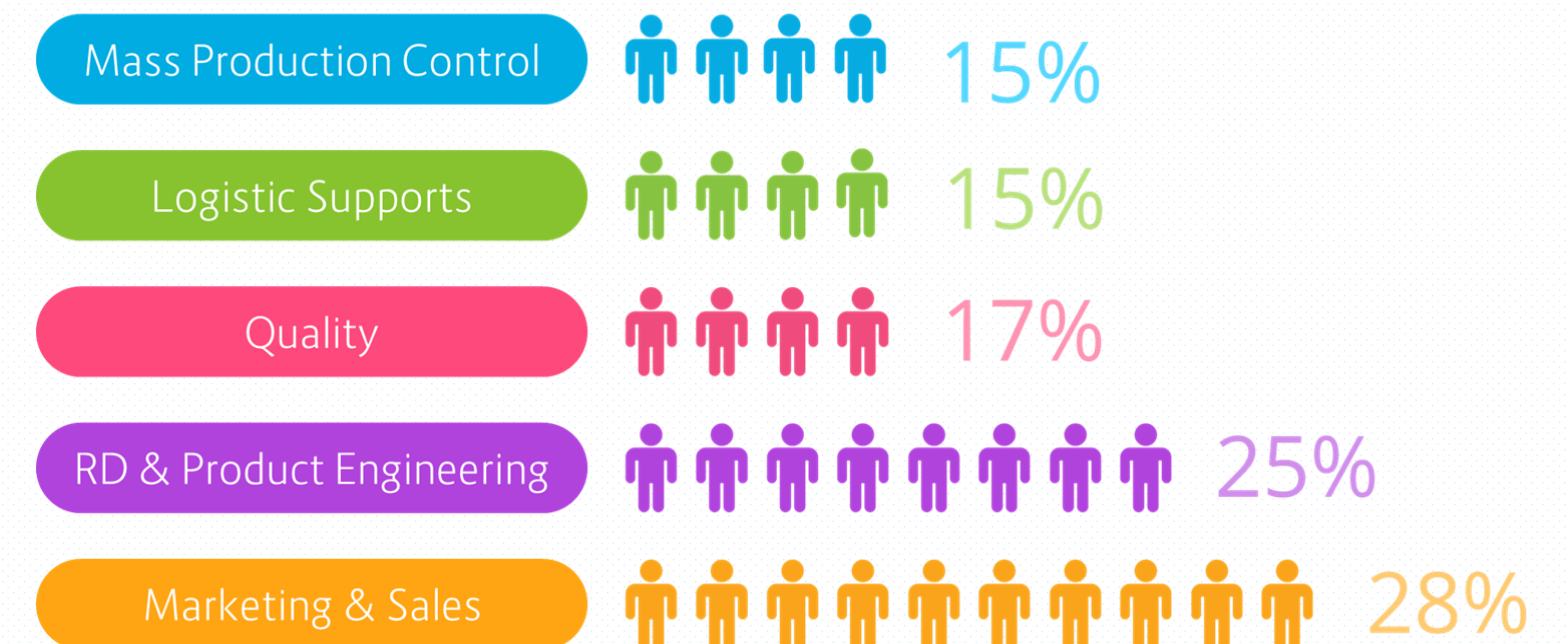
About us

- CET-MOS Corporation (CET-MOS), as a spin-off company from Chino-Excel Technology Corporation (CET)
- Inherited the technologies and experiences from CET over 40 years, successfully promote the first MOSFET to Taiwan market and keep as a pioneer in this field.
- We are committed to excellence in design and manufacturing high-quality Power MOSFET.

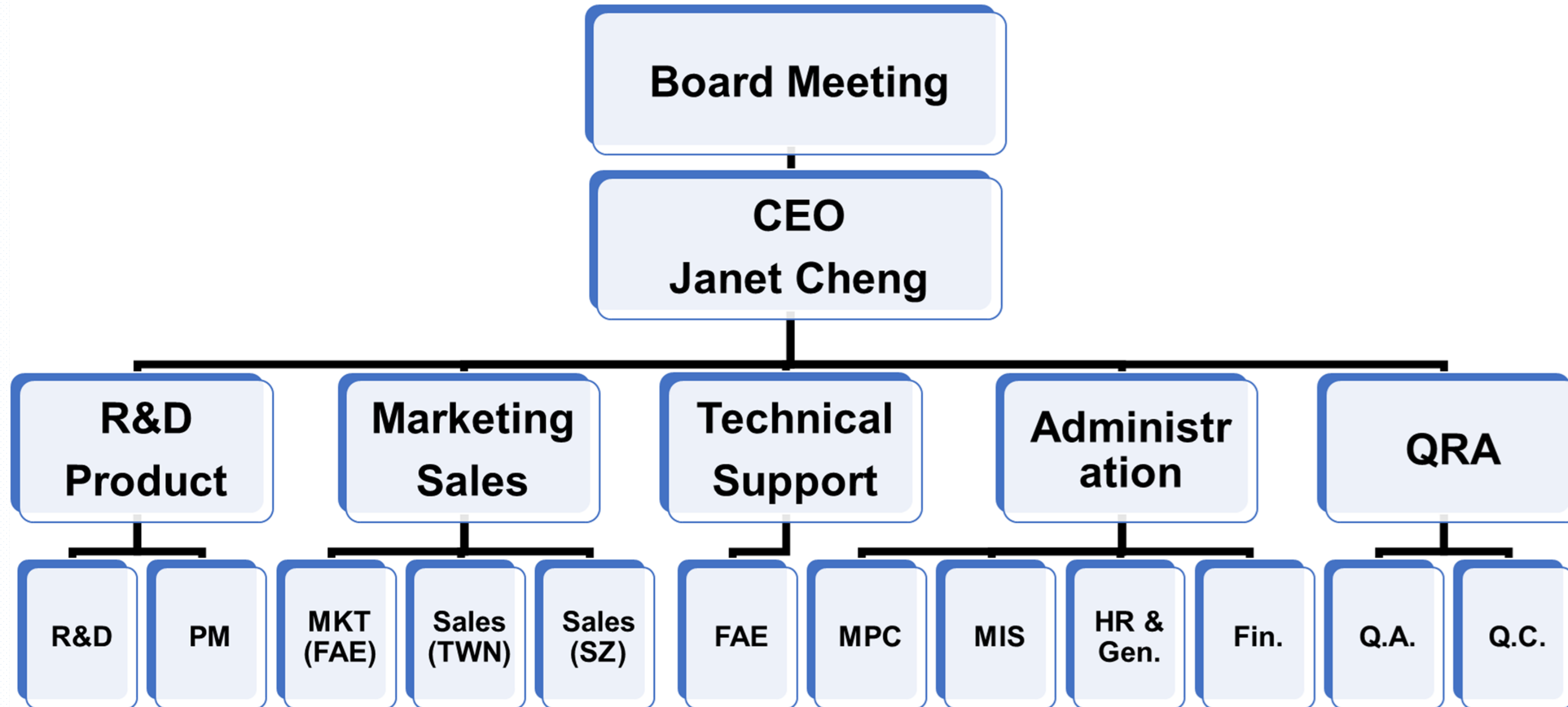


Company History

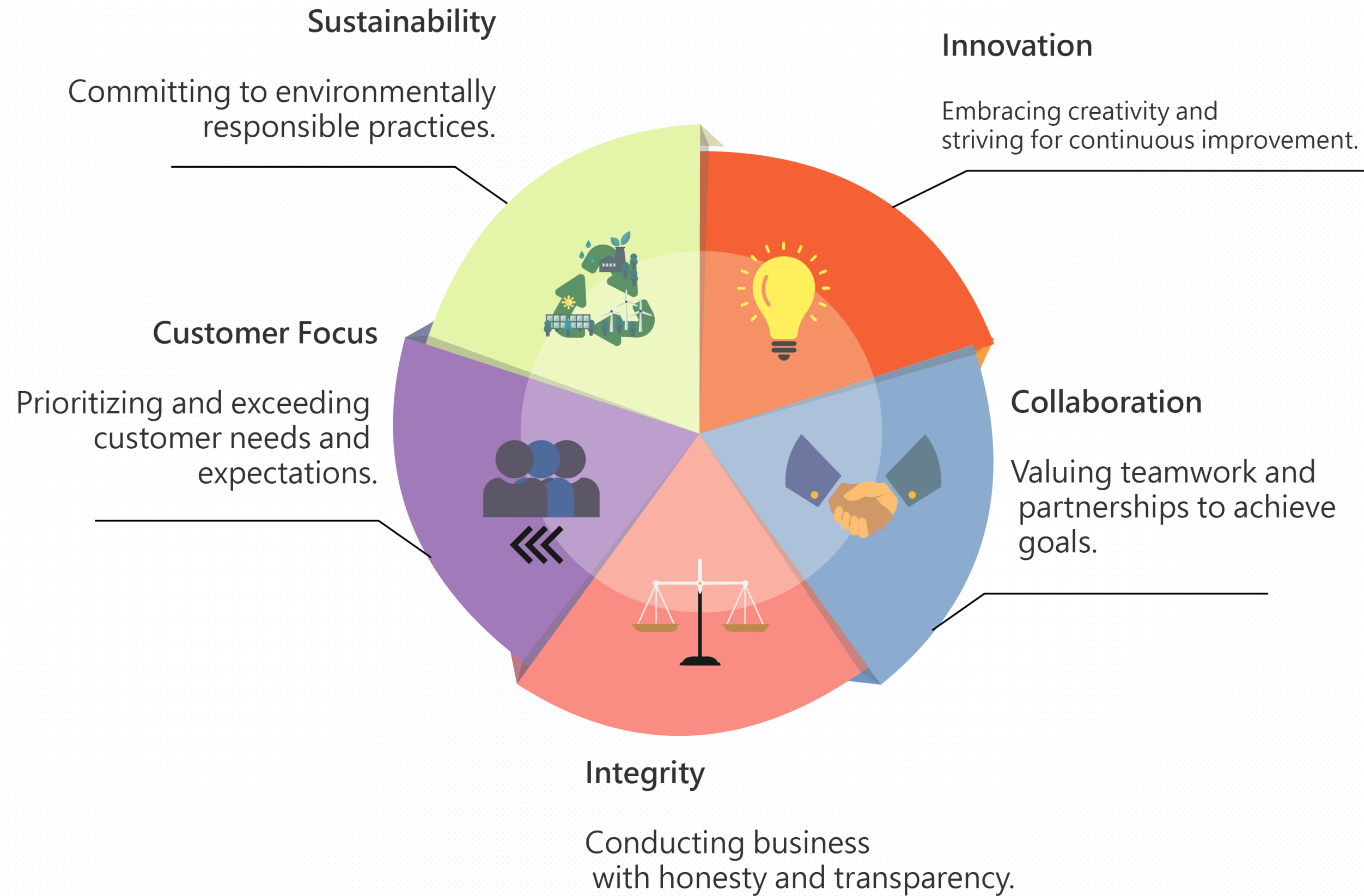
- **1984 Foundation**
 - ✓ 1st Assembly house location in the north of Taiwan.
- **1995 Approached Motherboard marketing**
 - ✓ 1st design house with MOSFET in Taiwan.
 - ✓ 1st filed the patent about MOSFET in Taiwan.
- **2005 Award of Green Management System from ASUS**
 - ✓ Top10 suppliers of Salcomp (Nokia's suppliers)
- **2012 Independent CET-MOS**
 - ✓ Move to new office.
 - ✓ Focus on discrete development.
- **2022 Till now~**
 - ✓ The best quality and reliability products.
 - ✓ The best cost/ performance ratio for various products.



Organization



Core Values



Our products and vision

DNV GL

MANAGEMENT SYSTEM
CERTIFICATE

Certificate No.: 6966-2003-AQ-RGC-RvA

Initial certification date: 17 January, 2003

Valid: 17 January, 2021 – 17 January, 2024

This is to certify that the management system of

CET-MOS Corporation

10F., No. 176, Jiankang Rd., Chung-Ho Dist., New Taipei City 23585, Taiwan
and the sites as mentioned in the appendix accompanying this certificate

has been found to conform to the Quality Management System standard:
ISO 9001:2015

This certificate is valid for the following scope:

Design and Production Management of Metal Oxide Silicon Field Effect Transistors

Place and date:
Shanghai, 21 December, 2020


MGMT. SYS.
RvA C 024
The RvA is a signatory to the IAF MLA

For the issuing office:
DNV GL – Business Assurance
Suite A, Building 9, No.1591 Hongqiao Road, Changning District, Shanghai 200336, P.R. China
TEL: +86 21 32799000


Zhu Hai Ming
Management Representative

Lack of fulfillment of conditions as set out in the Certification Agreement may render this Certificate invalid.

ACCREDITED UNIT: DNV GL Business Assurance B.V., ZWOLSEWEG 1, 2994 LB, BARENDRECHT, NETHERLANDS. TEL: +31102922689; assurance.dnvgl.com

ASSEMBLY PROCESS	ASSEMBLY TYPE	RoHS							REACH (SVHC)	Non-Halogen
		Pb	Cd	Hg	Cr+6	PBDEs	PBBs	Phthalates (DBP, BBP, DEHP, DIBP)		
Epoxy Process	SOT, SOP, TSOP, TSSOP, DFN...	V	V	V	V	V	V	V	V	V
Solder Process	TO, PPAK...	Pb>1000ppm Exemptions AnnexIII 7(a)	V	V	V	V	V	V	V	V

Quality of Life
Improvement

Enhancing living
standards



Technology
Solutions

Innovative tools
and systems

Productivity
Enhancement

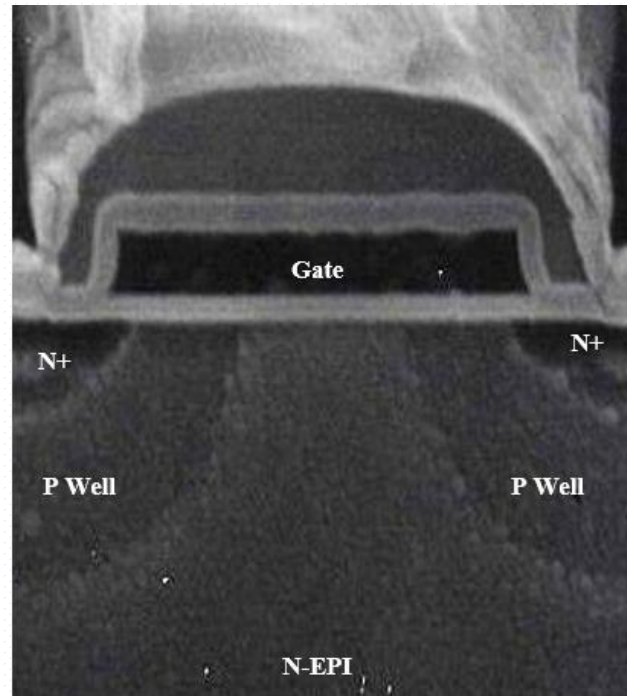
Boosting
efficiency and
output

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The Power of Expert

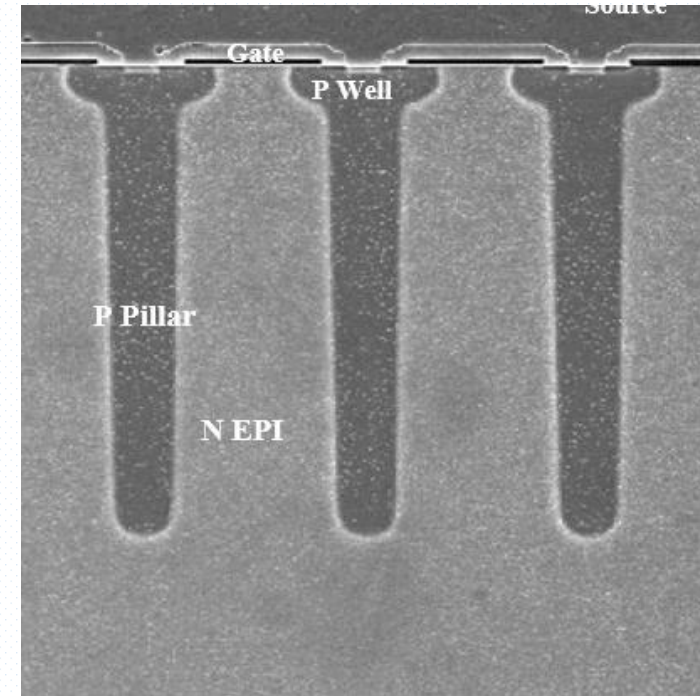
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MOSFETs Structure



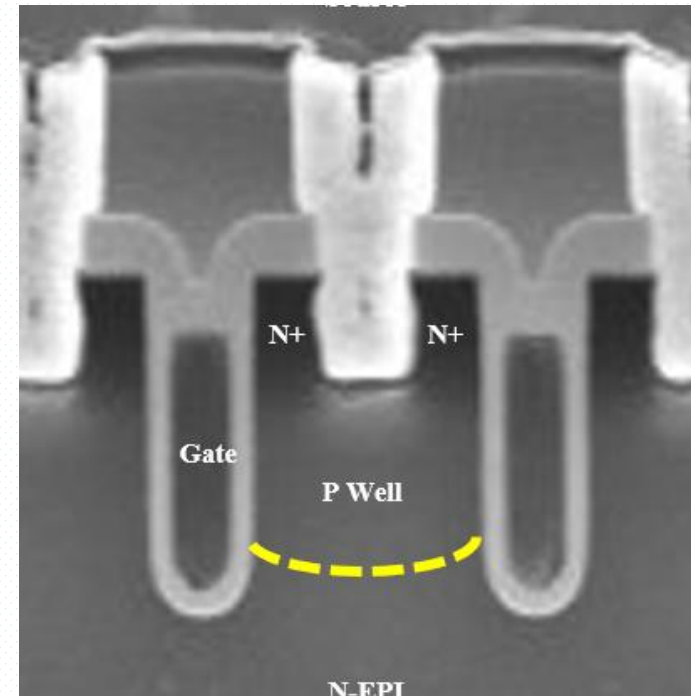
Planar Device

- High Voltage
- High Power
- Higher UIS
- Low Qgd



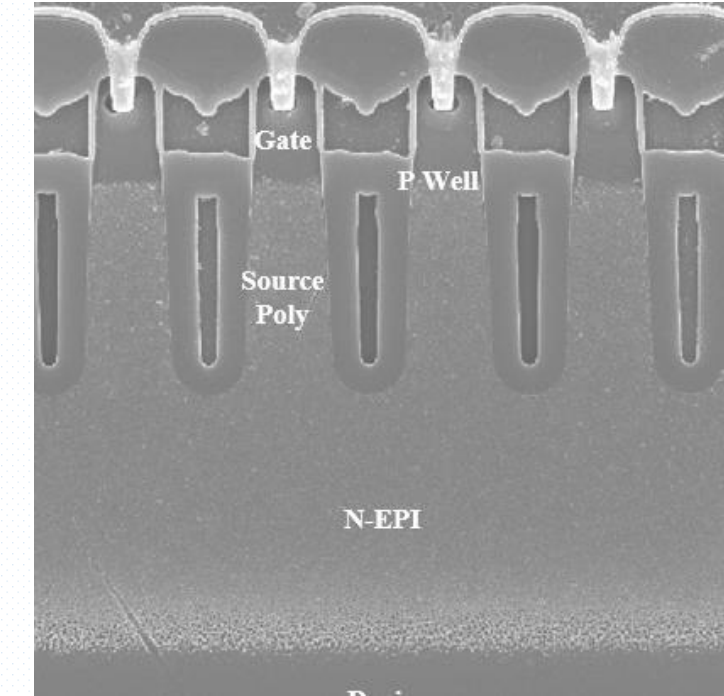
Super Junction Devices

- Planar Gate Structure
- High Drain-Source Breakdown
- Excellent $R_{ds(on)} \cdot Q_g$
- High Switching Speed



Trench Devices

- Higher Density
- Lower $R_{ds(on)}$
- Lower Qgd
- Suitable Die Size
- Lower Cost



Split Gate Devices

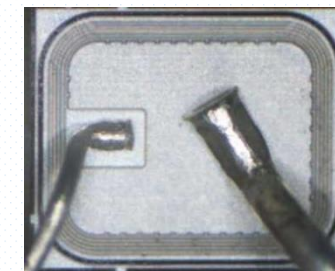
- Trench Gate Structure
- Low & Medium Drain-Source Breakdown
- Ultra Low $R_{ds(on)}$
- Lower Qgd/Qgs Ratio

Technology Roadmap



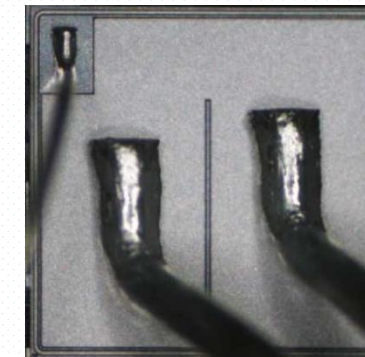
~Now

- Trench/ Split Gate MOSFETs (-200V~200V)
- IGBT Device (650V / 1200V)
- Super Junction Device (600V~900V)
- Planar MOSFET (30V~1500V)



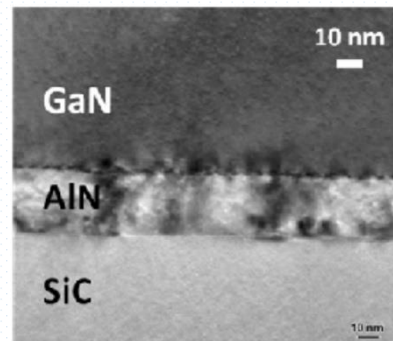
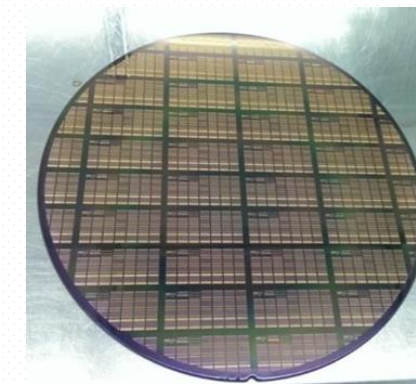
~2025

- Split Gate Device (G3 - 250V)
- Super Junction Device –
 - Multi-EPI and Deep trench both process development.
 - 900V with FRD
 - G2 and G3A process upgrade – Lower Rdson and Qrr/ Trr
- IGBT Device –
 - Module Development
 - Lower Vcesat and high speed
 - RC (G1) process
- GaN HEMT (D-mode 650V)
- SiC Diode / MOSFET (650V / 1200V)



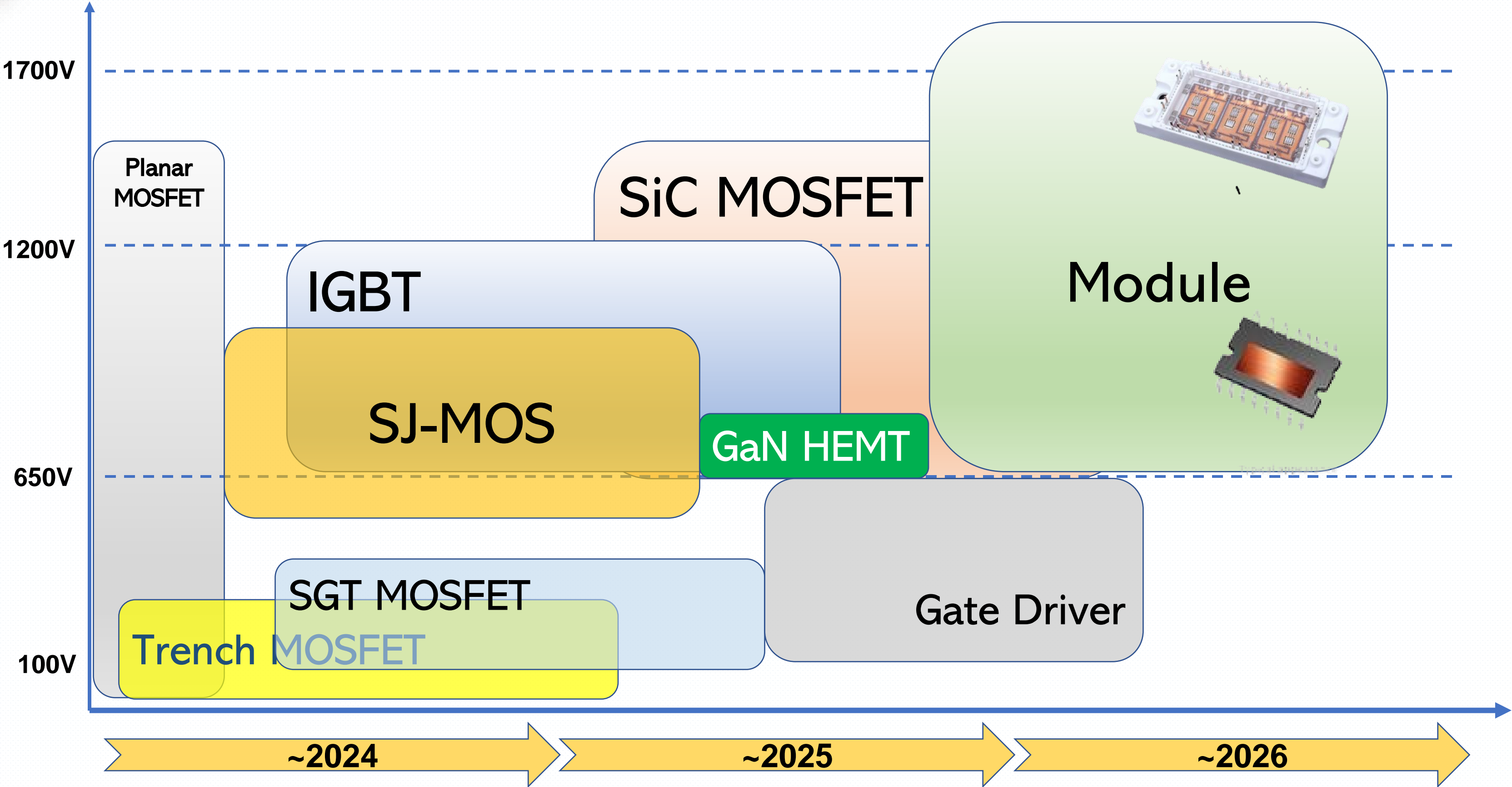
~2026

- Super Junction (G4) – Lower Rsp.
- SGT new process with 300mm
- IGBT process with 300mm
- SiC MOSFET (1700V)
- GaN HEMT (e-mode)

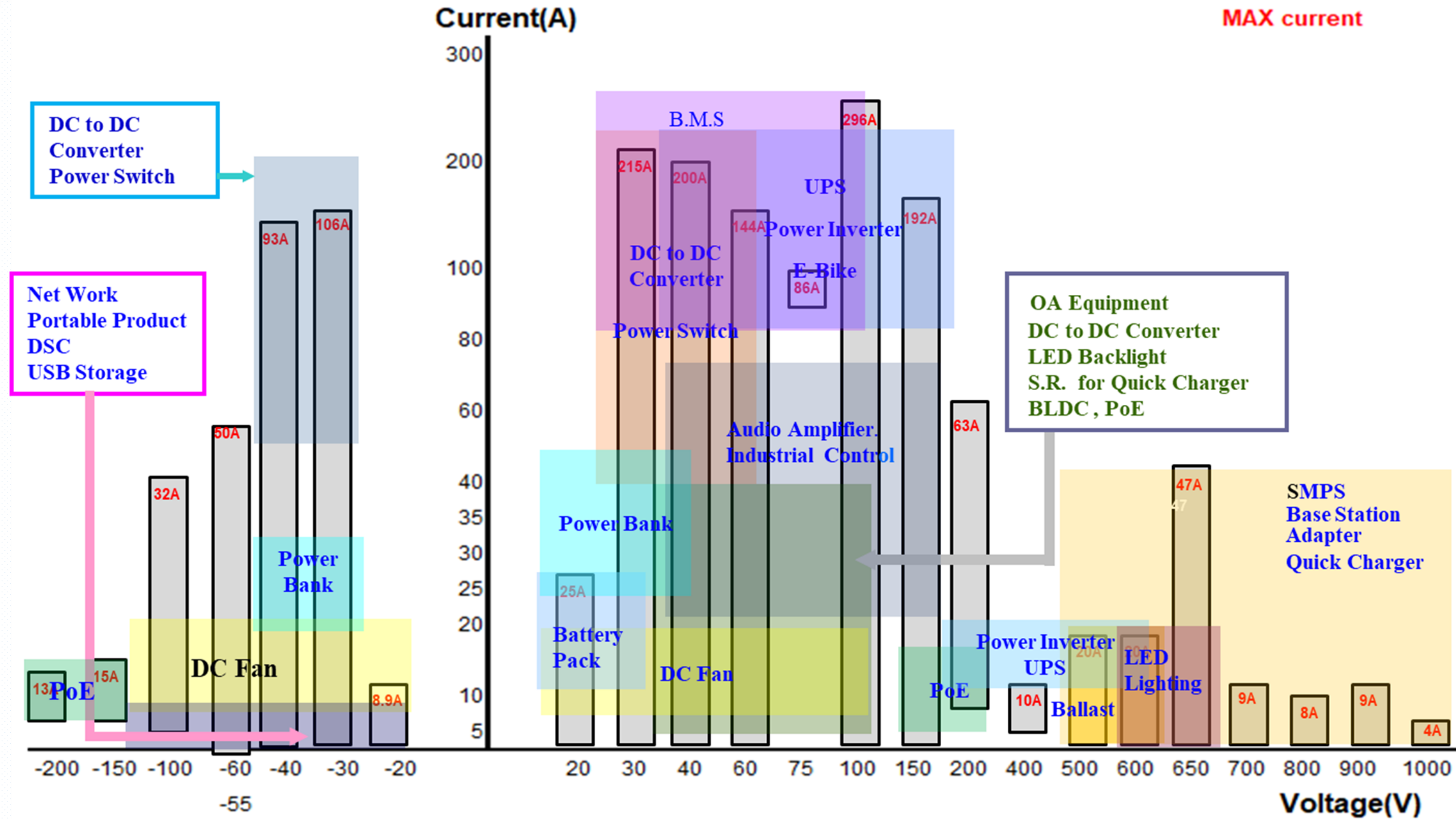


Core
Technology

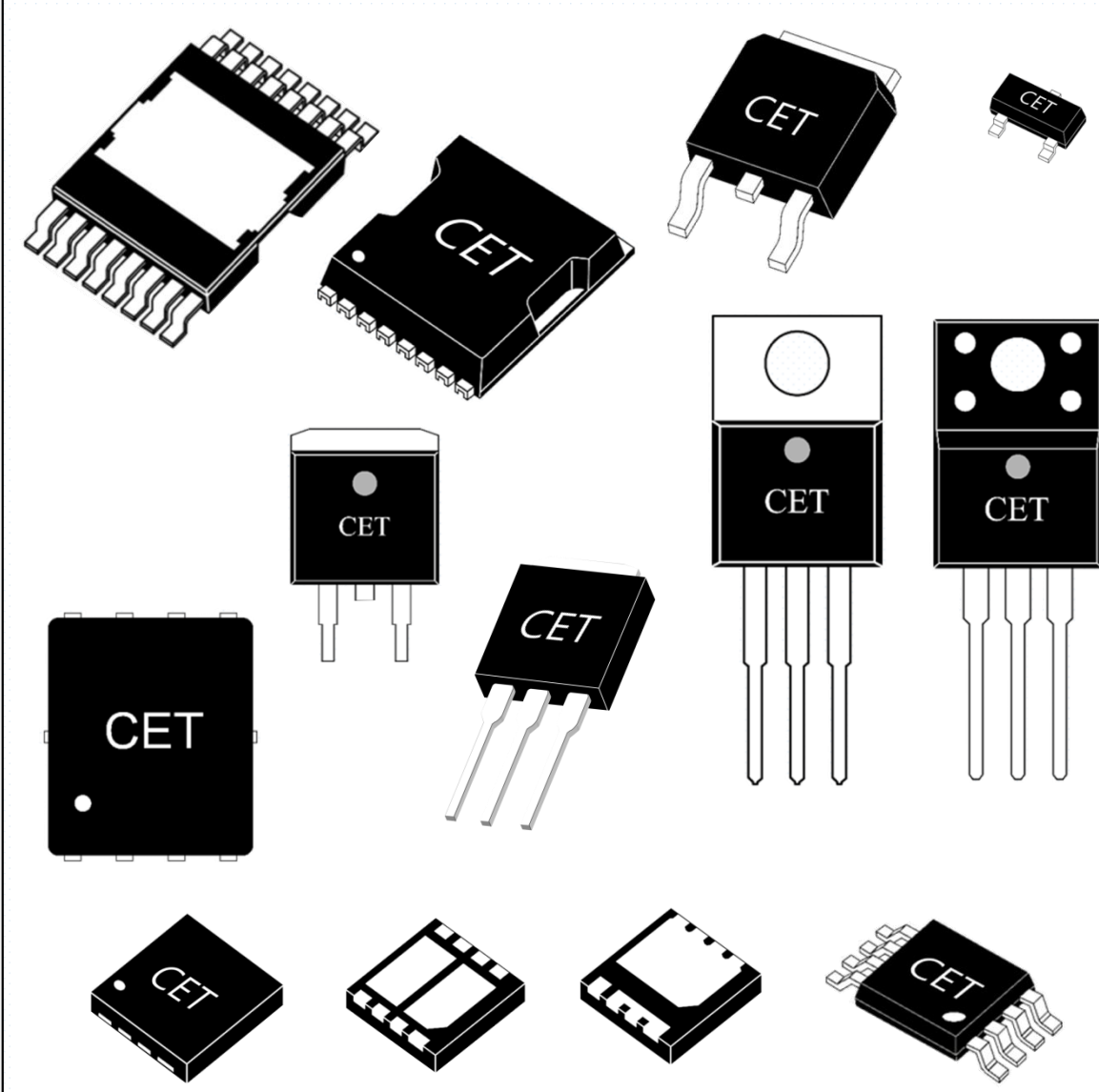
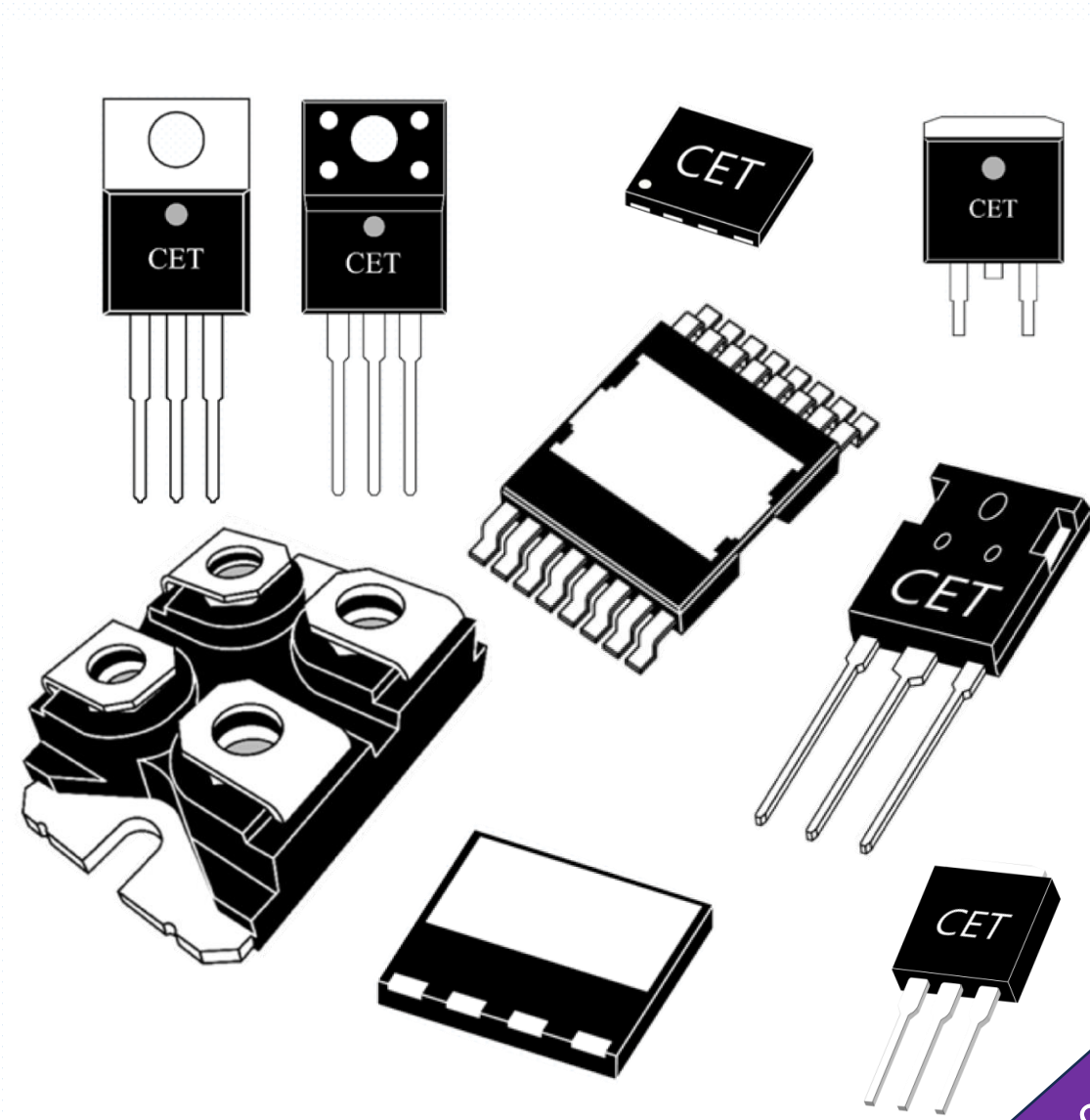
Products Development Roadmap



Application roadmap



Variety Package Types

Products	LV/ MV MOSFETs	HV MOSFETs
Vds (V)	-200 ~ 500	500 ~ 1000
Packages		

Variety MOSFETs for application

$\leq 30V$	40V~250V	$\geq 600V$
Low Voltage MOSFETs	Medium Voltage MOSFETs	High Voltage MOSFETs
<ul style="list-style-type: none"> · Battery protection · DC-DC Buck Conversion · Motor Control Drive · Load Switch · Mother Board/ Notebook PC · High/ Low Side · Graphic card · LED Monitor · Bluetooth · Server · Power over Ethernet 	<ul style="list-style-type: none"> · DC-DC Full Bridge Conversion · Synchronous Rectification · Motor Control Drive · Synchronous Rectification · Power Switch · DC-DC Buck Conversion · Motor Control Drive · Reverse Battery Protection · Base Station · Automotive · UPS · Power over Ethernet · Power tools 	<ul style="list-style-type: none"> · LLC Resonant Converters · Power Factor Correction · PV Solar Inverter · LED Lighting · Inverter Modules · Power Factor Correction · HEV/ EV · Home Appliances · Infrastructure

Top 10 application

- ◆ **Battery Protect**
 - Safety switches
- ◆ **Inverter/ Converter**
 - DC/AC conversion and load switches
- ◆ **Adapter/Charger/SPS**
 - Fly back/Forward /LLC switches
- ◆ **LED Lighting**
 - Buck/Boost switches
- ◆ **Network Communication**
 - DC/DC conversion & load switches
- ◆ **UPS**
 - High Power/Bridge switches
- ◆ **Motor/E-Bike**
 - High power Bridge switches
- ◆ **Monitor**
 - Switches
- ◆ **LED Display**
 - Switches
- ◆ **VGA**
 - DC/DC conversion & load switches



Products and Services



Strategic Alignment for future Success

Technological
Advancements



Customer Value



Strategic Alignment



Thank You!

